The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-21. (Canceled)

22. (Previously Presented) A semiconductor device comprising:

at least one thin film transistor comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of at least one of first and second wirings is aligned with at least one edge portion of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the at least one edge portion of the active layer, and

wherein the second insulating film is in contact with the insulating surface.

23. (Previously Presented) A semiconductor device comprising:

at least one thin film transistor comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of one of the first and second wirings is aligned with an edge of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the edge of the active layer, and

wherein the second insulating film is in contact with the insulating surface.

24. (Previously Presented) A semiconductor device comprising:

at least one thin film transistor comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of the first wiring is aligned with one of edge portions of the active layer, and a part of an edge portion of the second wiring is aligned with another one of the edge portions of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the edge portions of the active layer, and

wherein the second insulating film is in contact with the insulating surface.

25. (Canceled)

26. (Previously Presented) A semiconductor device according to claim 22, wherein the semiconductor device is a device selected from the group consisting of a

portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

27. (Previously Presented) A semiconductor device according to claim 23, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

28. (Previously Presented) A semiconductor device according to claim 24, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

29. (Previously Presented) A semiconductor device according to claim 22, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

30. (Previously Presented) A semiconductor device according to claim 23, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

31. (Previously Presented) A semiconductor device according to claim 24, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

32. (New) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of at least one of first and second wirings is aligned with at least one edge portion of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the at least one edge portion of the active layer, and

wherein the second insulating film is in contact with the insulating surface.

33. (New) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of one of the first and second wirings is aligned with an edge of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the edge of the active layer, and

wherein the second insulating film is in contact with the insulating surface.

34. (New) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of the first wiring is aligned with one of edge portions of the active layer, and a part of an edge portion of the second wiring is aligned with another one of the edge portions of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the edge portions of the active layer, and

wherein the second insulating film is in contact with the insulating surface.

35. (New) A semiconductor device according to claim 32, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

36. (New) A semiconductor device according to claim 33, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

37. (New) A semiconductor device according to claim 34, wherein the semiconductor device is a device selected from the group consisting of a portable

telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

38. (New) A semiconductor device according to claim 32, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

39. (New) A semiconductor device according to claim 33, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

40. (New) A semiconductor device according to claim 34, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.